ECOLE POLYTECHNIQUE FEDERALE DE LAUSANNE (EPFL)
Center of MicroNanoTechnology (CMI)

SOI WAFERS - SPECIFICATION SOI-380-2-150

Rev. 1.0 / 09.06.06

Bonded wafer

Growth method:	CZ
Bonding method:	Fusion bonding
Diameter:	100 ± 0.5mm
Primary Flat Orientation:	{110} ± 0.5°
Primary Flat Length:	32.5 ± 2.5 mm
Non-SOI edge area:	< 1.5mm (preferably 0mm if not affecting quality)
Edge Profile:	Rounded
Laser Marking:	380 2 150 SOI [xxx] according to large SEMI STD

Device Layer

Type / Dopant	P / Boron
Orientation incl. off-orientation:	{100} ± 0.5°
Resistivity:	1 – 10 Ohmcm
Thickness:	150 ± 0.7µm

Buried Oxide

Oxide Thickness:	2.00µm ± 3%

Handle Wafer

Type / Dopant	P / Boron
Orientation incl. off-orientation:	{100} ± 0.5°
Resistivity:	1 – 10 Ohmcm
Thickness:	380 ± 5µm
Back Surface:	Polished, without remaining oxide on backside
Laser Marking:	Wafers backside according to PO